

# PSMN034-100PS

N-channel 100 V 34.5 mΩ standard level MOSFET in TO220.

Rev. 02 — 1 March 2010

Objective data sheet

## 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in TO220 package qualified to 175°C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

### 1.3 Applications

- DC-to-DC converters
- Motor control
- Load switching
- Server power supplies

### 1.4 Quick reference data

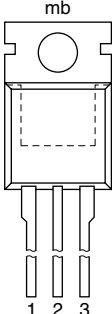
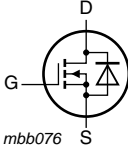
Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$	-	-	100	V
$I_D$	drain current	$T_{mb} = 25\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; see <a href="#">Figure 1</a>	-	-	32	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>	-	-	86	W
$T_j$	junction temperature		-55	-	175	°C
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ °C}$ ; $I_D = 32\text{ A}$ ; $V_{sup} \leq 100\text{ V}$ ; unclamped; $R_{GS} = 50\text{ }\Omega$	-	-	42	mJ
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10\text{ V}$ ; $I_D = 15\text{ A}$ ;	-	6.9	-	nC
$Q_{G(tot)}$	total gate charge	$V_{DS} = 50\text{ V}$ ; see <a href="#">Figure 12</a> and <a href="#">13</a>	-	23.8	-	nC
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$ ; $I_D = 15\text{ A}$ ; $T_j = 100\text{ °C}$ ; see <a href="#">Figure 11</a>	-	-	62	mΩ
		$V_{GS} = 10\text{ V}$ ; $I_D = 15\text{ A}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 16</a>	-	29.3	34.5	mΩ



## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

**SOT78 (TO-220AB)**

## 3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
PSMN034-100PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

## 4. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

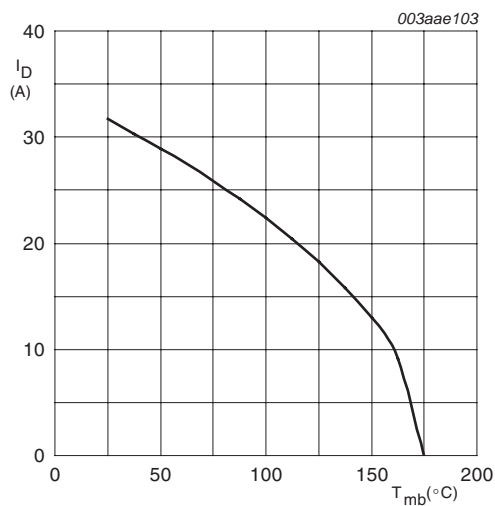
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$	-	100	V
$V_{DGR}$	drain-gate voltage	$T_j \leq 175\text{ °C}$ ; $T_j \geq 25\text{ °C}$ ; $R_{GS} = 20\text{ k}\Omega$	-	100	V
$V_{GS}$	gate-source voltage		-20	20	V
$I_D$	drain current	$V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ °C}$ ; see <a href="#">Figure 1</a>	-	22	A
		$V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 1</a>	-	32	A
$I_{DM}$	peak drain current	$t_p \leq 10\text{ }\mu\text{s}$ ; pulsed; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 3</a>	-	127	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>	-	86	W
$T_{stg}$	storage temperature		-55	175	°C
$T_j$	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C

### Source-drain diode

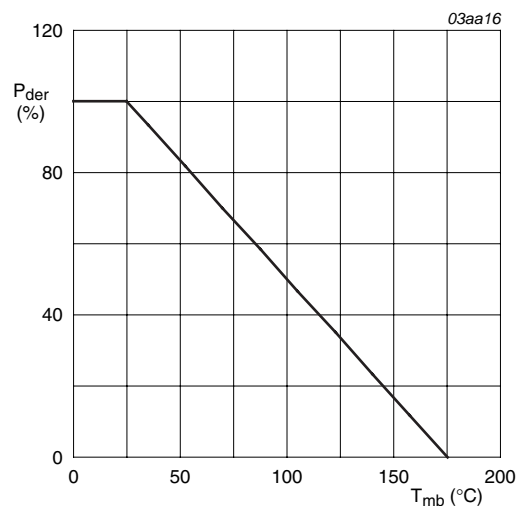
$I_S$	source current	$T_{mb} = 25\text{ °C}$	-	32	A
$I_{SM}$	peak source current	$t_p \leq 10\text{ }\mu\text{s}$ ; pulsed; $T_{mb} = 25\text{ °C}$	-	127	A

### Avalanche ruggedness

$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$ ; $T_{j(\text{init})} = 25\text{ °C}$ ; $I_D = 32\text{ A}$ ; $V_{sup} \leq 100\text{ V}$ ; unclamped; $R_{GS} = 50\text{ }\Omega$	-	42	mJ
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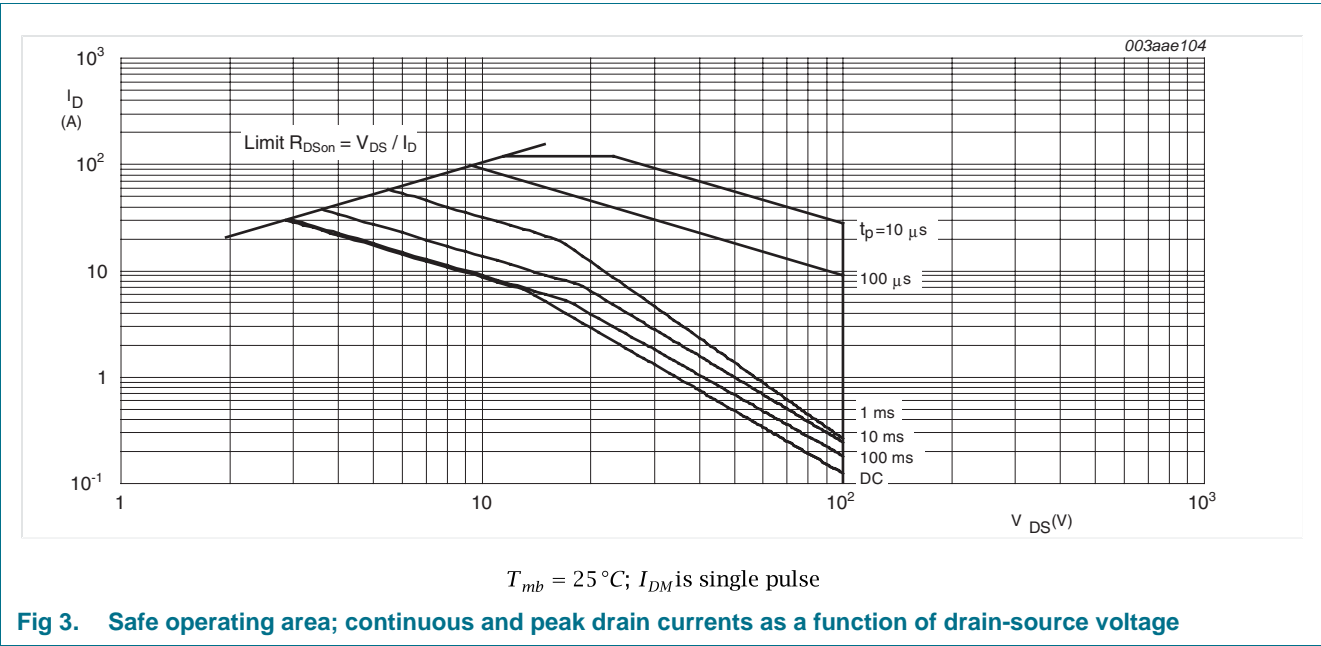


**Fig 1. Continuous drain current as a function of mounting base temperature**



$$P_{der} = \frac{P_{tot}}{P_{tot(25\text{ °C})}} \times 100\%$$

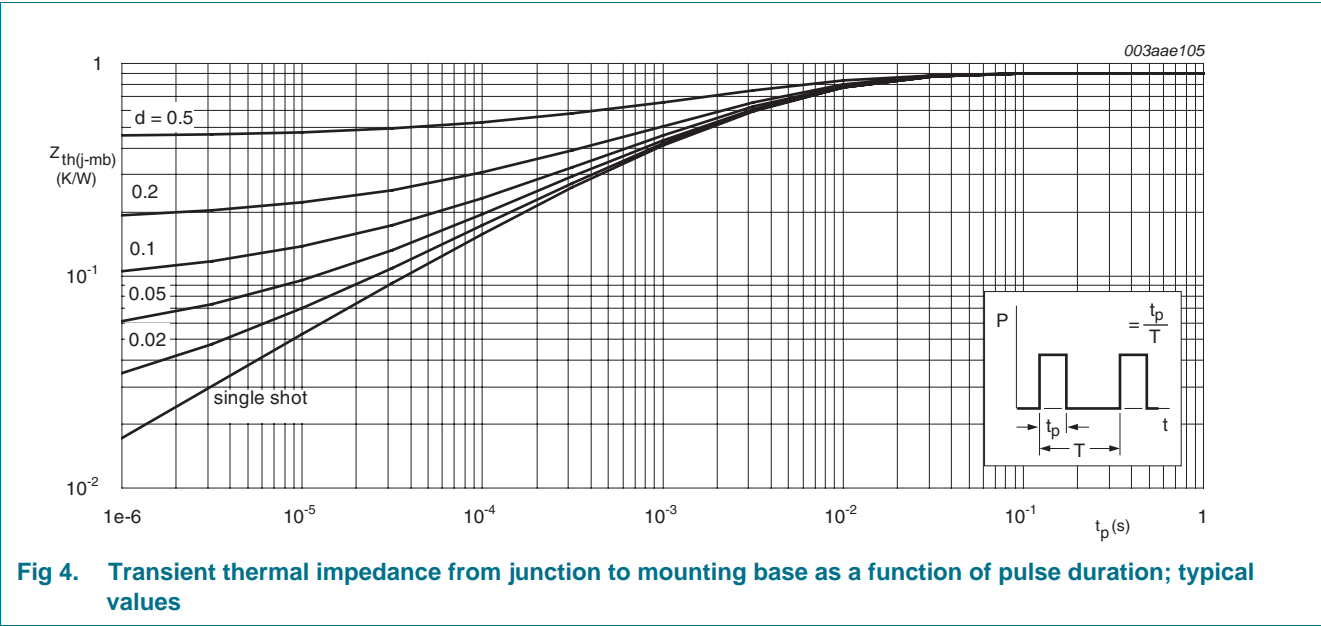
**Fig 2. Normalized total power dissipation as a function of mounting base temperature**



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 4</a>	-	0.9	1.7	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in free air	-	50	-	K/W



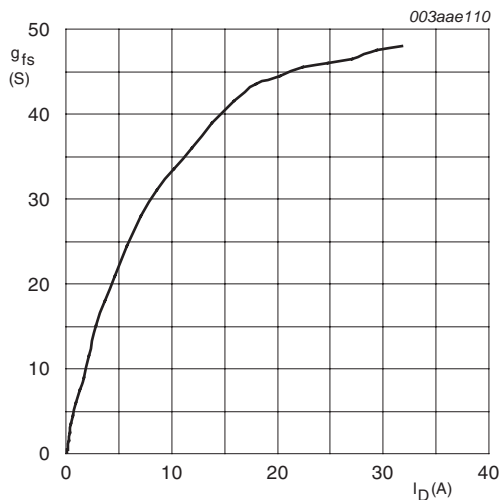
## 6. Characteristics

**Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^{\circ}\text{C}$	90	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^{\circ}\text{C}$	100	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^{\circ}\text{C}$ ; see <a href="#">Figure 9</a>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^{\circ}\text{C}$ ; see <a href="#">Figure 10</a> and <a href="#">9</a>	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^{\circ}\text{C}$ ; see <a href="#">Figure 9</a> and <a href="#">10</a>	-	-	4.8	V
$I_{DSS}$	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^{\circ}\text{C}$	-	-	50	$\mu\text{A}$
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^{\circ}\text{C}$	-	0.02	1	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^{\circ}\text{C}$	-	10	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^{\circ}\text{C}$	-	10	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ }^{\circ}\text{C}$ ; see <a href="#">Figure 11</a>	-	-	62	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 \text{ }^{\circ}\text{C}$ ; see <a href="#">Figure 11</a>	-	82.1	96	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ }^{\circ}\text{C}$ ; see <a href="#">Figure 16</a>	-	29.3	34.5	mΩ
$R_G$	internal gate resistance (AC)	$f = 1 \text{ MHz}$	-	1	-	Ω
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 15 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V}$ ; see <a href="#">Figure 12</a> and <a href="#">13</a>	-	23.8	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	19	-	nC
$Q_{GS}$	gate-source charge	$I_D = 15 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V}$ ; see <a href="#">Figure 12</a> and <a href="#">13</a>	-	5.5	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge	$I_D = 15 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V}$ ; see <a href="#">Figure 12</a>	-	3.6	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	1.9	-	nC
$Q_{GD}$	gate-drain charge	$I_D = 15 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V}$ ; see <a href="#">Figure 12</a> and <a href="#">13</a>	-	6.9	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$V_{DS} = 50 \text{ V}$ ; see <a href="#">Figure 12</a> and <a href="#">13</a>	-	4.4	-	V
$C_{iss}$	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ }^{\circ}\text{C}$ ; see <a href="#">Figure 14</a>	-	1201	-	pF
$C_{oss}$	output capacitance		-	94	-	pF
$C_{rss}$	reverse transfer capacitance		-	61	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 3.3 \text{ } \Omega; V_{GS} = 10 \text{ V}$ ; $R_{G(ext)} = 4.7 \text{ } \Omega; T_j = 25 \text{ }^{\circ}\text{C}$	-	12	-	ns
$t_r$	rise time		-	10	-	ns
$t_{d(off)}$	turn-off delay time		-	28	-	ns
$t_f$	fall time		-	9	-	ns

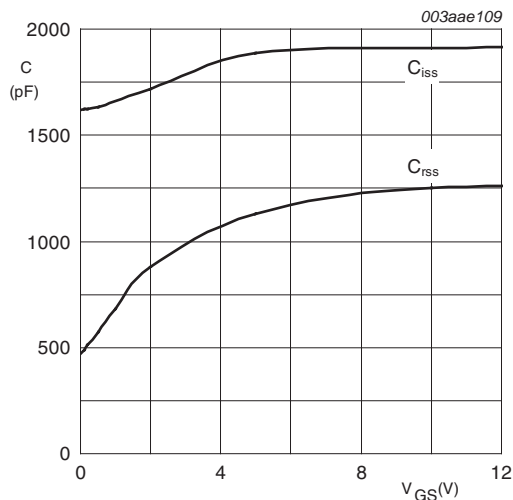
Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode						
$V_{SD}$	source-drain voltage	$I_S = 15\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 17</a>	-	0.85	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 5\text{ A}$ ; $di_S/dt = 100\text{ A/}\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ;	-	38	-	ns
$Q_r$	recovered charge	$V_{DS} = 50\text{ V}$	-	59	-	nC



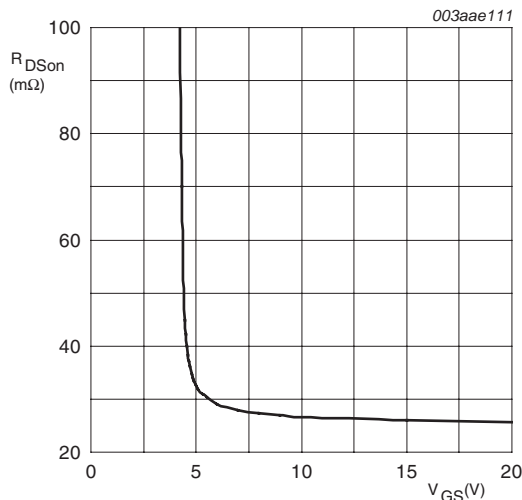
$T_j = 25\text{ °C}$ ;  $V_{DS} = 10\text{ V}$

Fig 5. Forward transconductance as a function of drain current; typical values



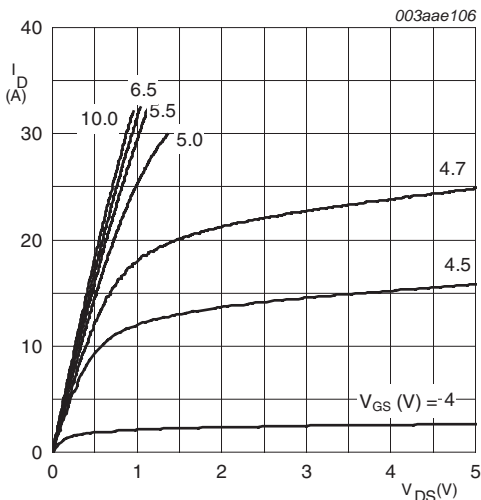
$V_{DS} = 0\text{ V}$ ;  $f = 1\text{ MHz}$

Fig 6. Input and reverse capacitances as a function of gate-source voltage; typical values



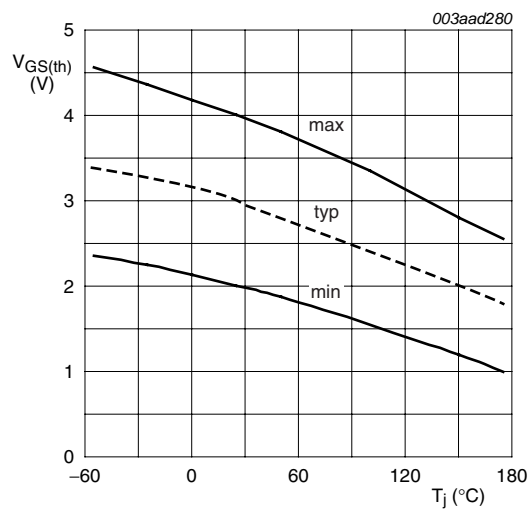
$T_j = 25\text{ °C}$ ;  $I_D = 5\text{ A}$

Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



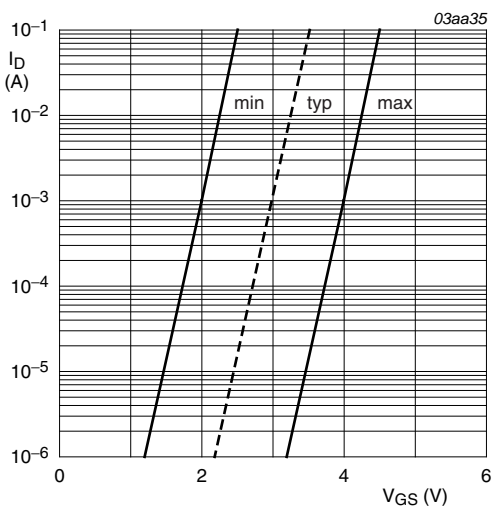
$T_j = 25\text{ °C}$ ;  $t_p = 300\text{ }\mu\text{s}$

Fig 8. Output characteristics: drain current as a function of drain-source voltage; typical values



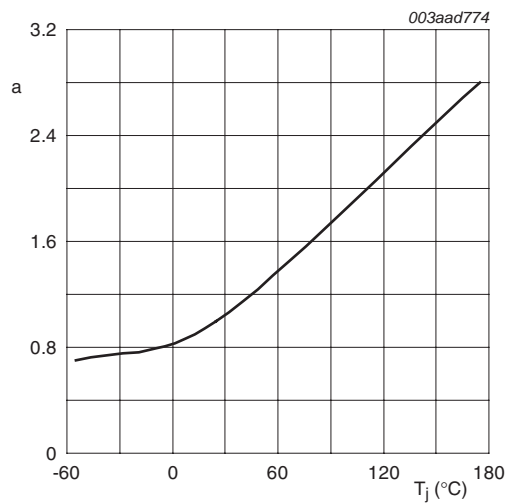
$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

Fig 9. Gate-source threshold voltage as a function of junction temperature



$T_j = 25 \text{ °C}; V_{DS} = 5 \text{ V}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage



$$a = \frac{R_{DSon}}{R_{DSon(25 \text{ °C})}}$$

Fig 11. Normalized drain-source on-state resistance factor as a function of junction temperature

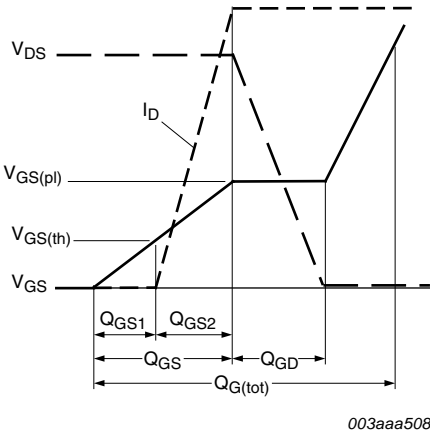
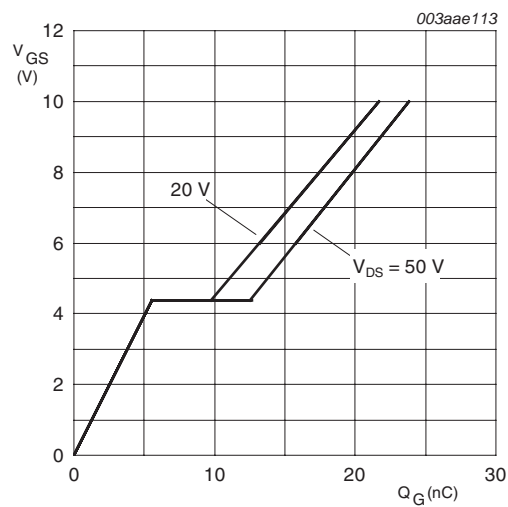


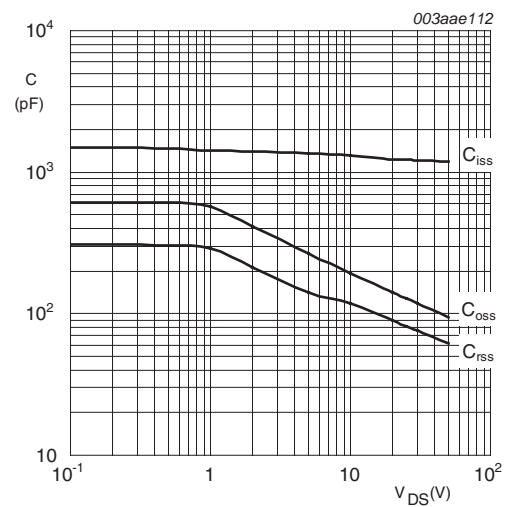
Fig 12. Gate charge waveform definitions





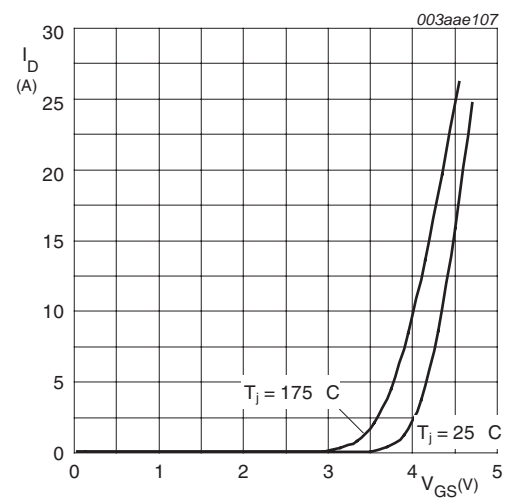
$T_j = 25^\circ\text{C}; I_D = 15\text{A}$

Fig 13. Gate-source voltage as a function of gate charge; typical values



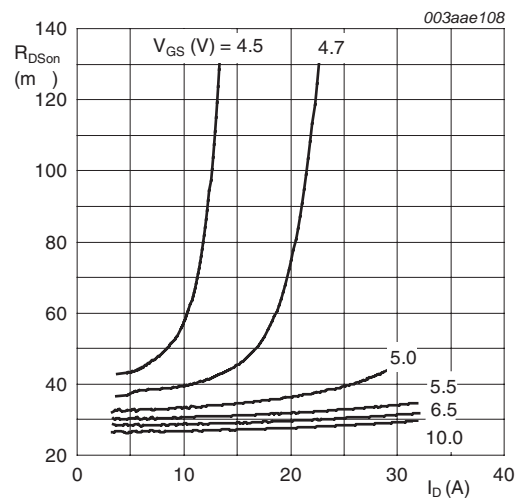
$V_{GS} = 0\text{V}; F = 1\text{MHz}$

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$T_j = 25^\circ\text{C}; V_{DS} = 15\text{V}$

Fig 15. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$T_j = 25^\circ\text{C}; t_p = 300\mu\text{s}$

Fig 16. Drain-source on-state resistance as a function of drain current; typical values

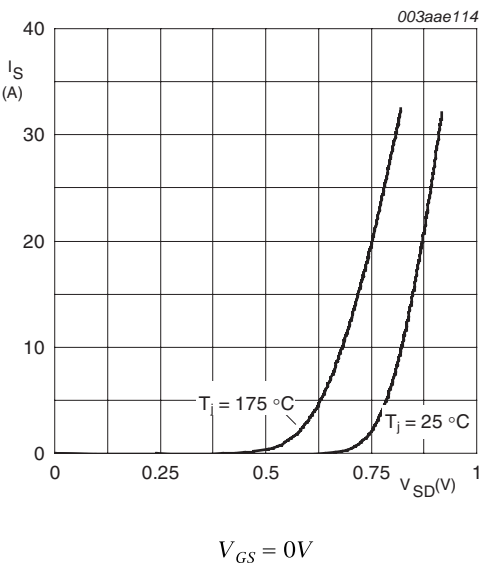


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB SOT78

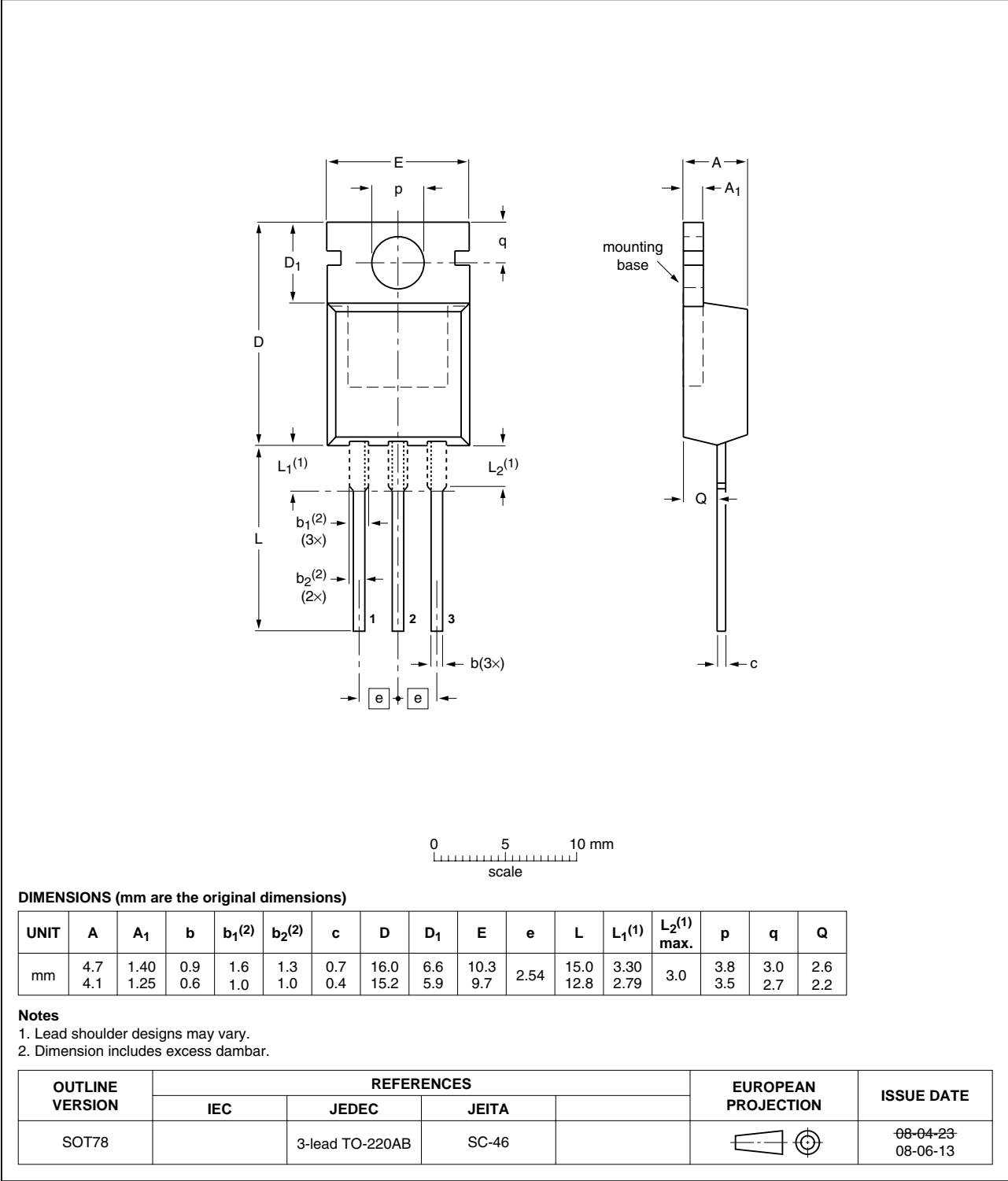


Fig 18. Package outline SOT78 (TO-220AB)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN034-100PS_2	20100301	Objective data sheet	-	PSMN034-100PS_1
Modifications:	• Various changes to content.			
PSMN034-100PS_1	20100218	Objective data sheet	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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Date of release: 1 March 2010

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